

PALM INTRANET

Day : Saturday  
Date: 4/29/2006  
Time: 19:49:53

**Inventor Name Search Result**

Your Search was:

Last Name = JOSHI

First Name = POORAN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09855549</u>	Not Issued	168	05/16/2001	Fabrication of pure and modified Ta2O5 thin film with enhanced properties for microwave communication, dynamic random access memory and integrated electronic applications	JOSHI, POORAN C.
<u>09939420</u>	<u>6759683</u>	150	08/27/2001	FORMULATION AND FABRICATION OF AN IMPROVED NI BASED COMPOSITE OHMIC CONTACT TO N-SIC FOR HIGH TEMPERATURE AND HIGH POWER DEVICE APPLICATIONS	JOSHI, POORAN C.
<u>10661547</u>	<u>6919283</u>	150	09/15/2003	FABRICATION OF PURE AND MODIFIED TA2O5 THIN FILM WITH ENHANCED PROPERTIES FOR MICROWAVE COMMUNICATION, DYNAMIC RANDOM ACCESS MEMORY AND INTEGRATED ELECTRONIC APPLICATIONS	JOSHI, POORAN C.
<u>10884580</u>	Not Issued	41	07/06/2004	Formulation and fabrication of an improved Ni based composite ohmic contact to n-Sic for high temperature and high power device applications	JOSHI, POORAN C.
<u>60205140</u>	Not Issued	159	05/18/2000	Fabrication of pure and modified Ta2O5 thin films with enhanced properties for microwave communication, dynamic random access memory and integrated electronic applications	JOSHI, POORAN C.
<u>08852253</u>	Not Issued	161	05/06/1997	PROCESS FOR FABRICATING SOLID-SOLUTION OF LAYERED PEROVSKITE MATERIALS FOR NONVOLATILE RANDOM ACCESS MEMORY AND INTEGRATED ELECTRONIC APPLICATIONS	JOSHI, POORAN C.
<u>09192619</u>	<u>6071555</u>	150	11/05/1998	FERROELECTRIC THIN FILM COMPOSITES MADE BY METALORGANIC DECOMPOSITION	JOSHI, POORAN C.
<u>10295400</u>	<u>6902960</u>	150	11/14/2002	OXIDE INTERFACE AND A METHOD FOR FABRICATING OXIDE THIN	JOSHI, POORAN CHANDRA

				FILMS	
<u>10295579</u>	<u>6689646</u>	150	11/14/2002	PLASMA METHOD FOR FABRICATING OXIDE THIN FILMS	JOSHI, POORAN CHANDRA
<u>10801374</u>	Not Issued	71	03/15/2004	Method for fabricating oxide thin films	JOSHI, POORAN CHANDRA
<u>10801377</u>	Not Issued	71	03/15/2004	Deposition oxide with improved oxygen bonding	JOSHI, POORAN CHANDRA
<u>10805158</u>	Not Issued	41	03/19/2004	Charge trap non-volatile memory structure for 2 bits per transistor	JOSHI, POORAN CHANDRA
<u>10812591</u>	Not Issued	71	03/29/2004	High density plasma process for the formation of silicon dioxide on silicon carbide substrates	JOSHI, POORAN CHANDRA
<u>10871939</u>	Not Issued	61	06/17/2004	High density plasma process for silicon thin films	JOSHI, POORAN CHANDRA
<u>11013605</u>	Not Issued	30	12/15/2004	High-density plasma hydrogenation	JOSHI, POORAN CHANDRA
<u>11046571</u>	Not Issued	41	01/28/2005	Thin film oxide interface	JOSHI, POORAN CHANDRA
<u>11066713</u>	Not Issued	30	02/24/2005	High-luminescence silicon electroluminescence device	JOSHI, POORAN CHANDRA
<u>11139726</u>	Not Issued	30	05/26/2005	High-density plasma oxidation for enhanced gate oxide performance	JOSHI, POORAN CHANDRA
<u>11218111</u>	Not Issued	30	09/01/2005	High density plasma grown silicon nitride	JOSHI, POORAN CHANDRA
<u>11264979</u>	Not Issued	30	11/02/2005	High-density plasma multilayer gate oxide	JOSHI, POORAN CHANDRA
<u>11327612</u>	Not Issued	30	01/06/2006	Enhanced thin-film oxidation process	JOSHI, POORAN CHANDRA

Inventor Search Completed: No Records to Display.

**Search Another: Inventor**

<b>Last Name</b>	<b>First Name</b>	<b>Search</b>
joshi	pooran	

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## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L5	194	((HD ADJ ICP) (high adj density adj inductive\$2 adj coupl\$3 adj plasma\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:23
L7	9302	((ECR) (electron adj cyclotron adj resonance)) with plasma\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:24
L8	117	(cathode adj coupl\$3) with plasma\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:25
L9	251	(5 7 8) with (oxidiz\$5 oxidat\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:27
L10	144	9 and (temperature\$1 with plasma\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:27
L11	121	10 and (oxide\$1 near3 (Zn zinc Si silicon C carbon Ge germanium Sn tin Pb lead))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:29
L12	31	11 and ((diffus\$3 bond\$3) with oxygen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 18:30